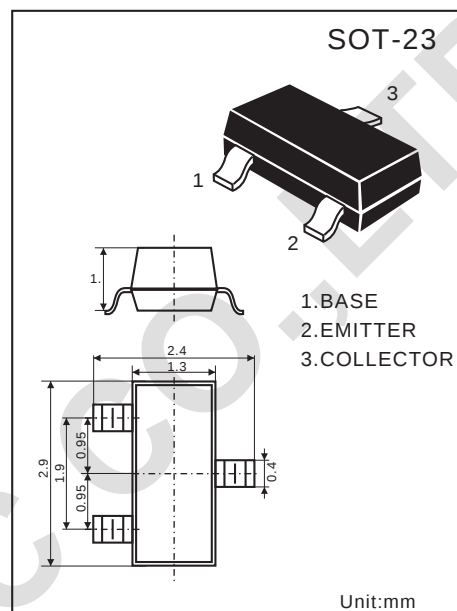
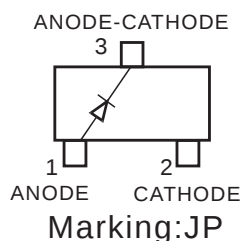


SWITCHING DIODE

Features

- Power dissipation
 P_D : 225 mW ($T_{amb}=25^\circ\text{C}$)
- Pluse Drain
 I_F : 200 mA
- Reverse Voltage
 V_R : 120V
- Operating and storage junction temperature range
 T_j, T_{stg} : -55°C to $+150^\circ\text{C}$



Electro-Optical Characteristics

($T_a=25^\circ\text{C}$)

Parameter	Symbol	Test Condition	MIN.	MAX.	Unit
Reverse breakdown voltage	$V_{(BR)}$	$I_R=100\mu\text{A}$	120		V
Reverse Voltage leakage current	I_R	$V_R=100\text{V}$		0.1	μA
Forward Voltage	V_F	$I_F=100\text{mA}$ $I_F=200\text{mA}$		1000 1250	mV
Diode Capacitance	C_D	$V_R=0\text{V}$ $f=1\text{MHz}$		5	pF
Reverse Recovery Time	t_{rr}			50	nS

Typical Characteristics

